

# ESA Strategy on Radiation Testing Capabilities

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NICA workshop September 16, 2021



## EUROPE'S GATEWAY TO SPACE

### WHAT

22 Member States, 5000 employees

### WHY

Exploration and use of space for exclusively peaceful purposes

### WHERE

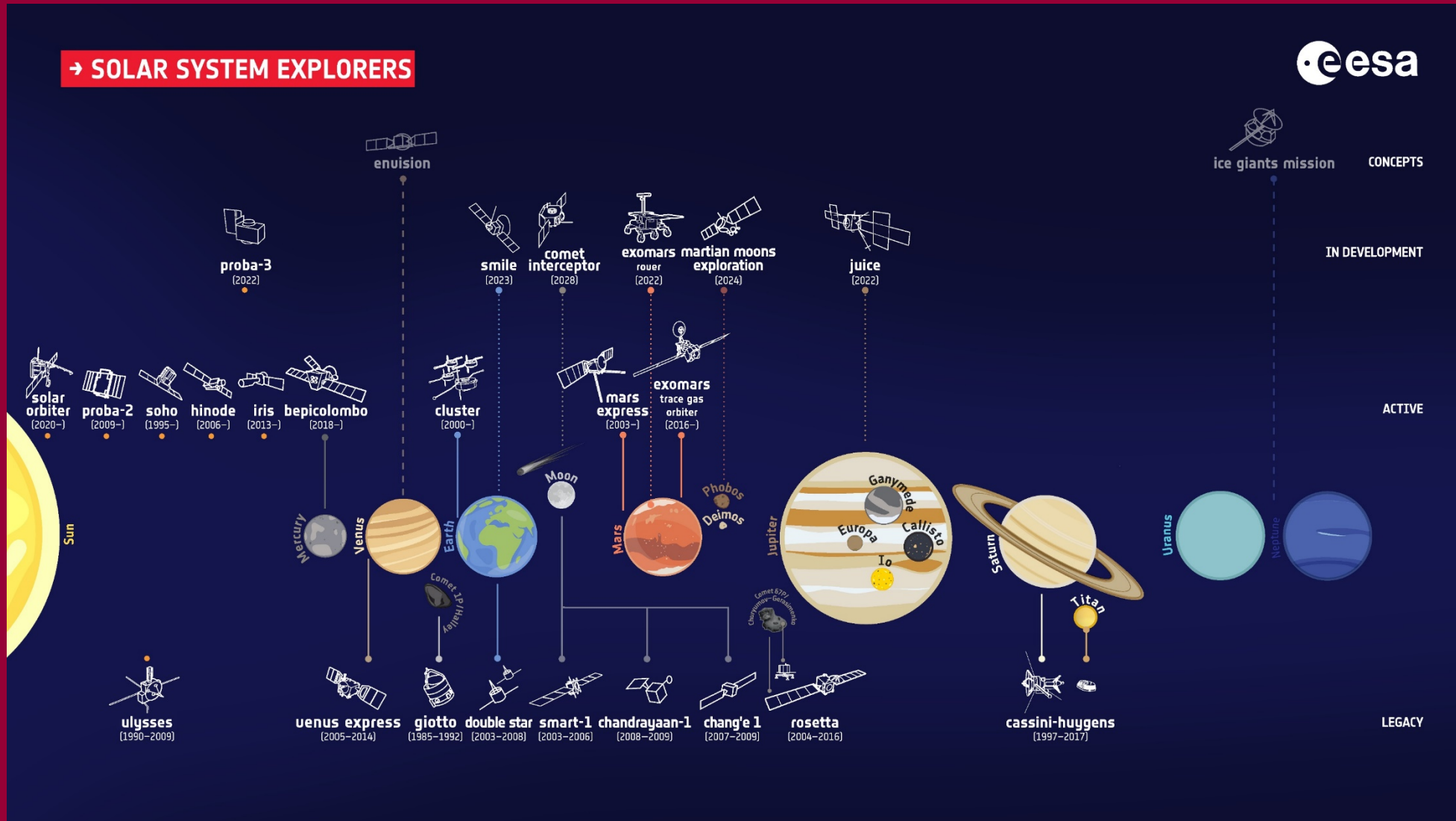
HQ in Paris, 7 sites across Europe and a spaceport in French Guiana

### HOW MUCH

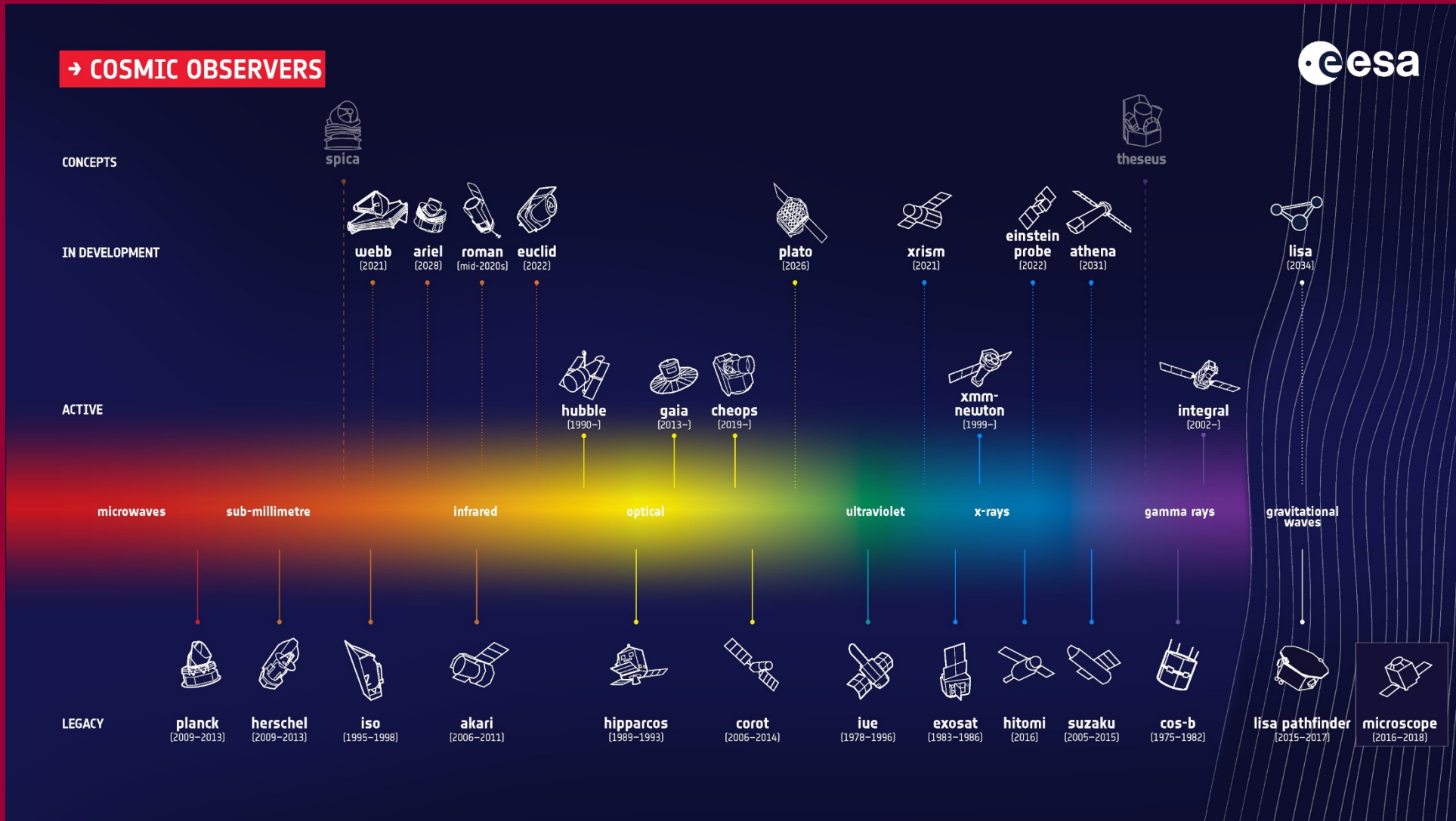
€6.68 billion = €12 per European per year



# Some of Today and Tomorrow's Science Missions (1)

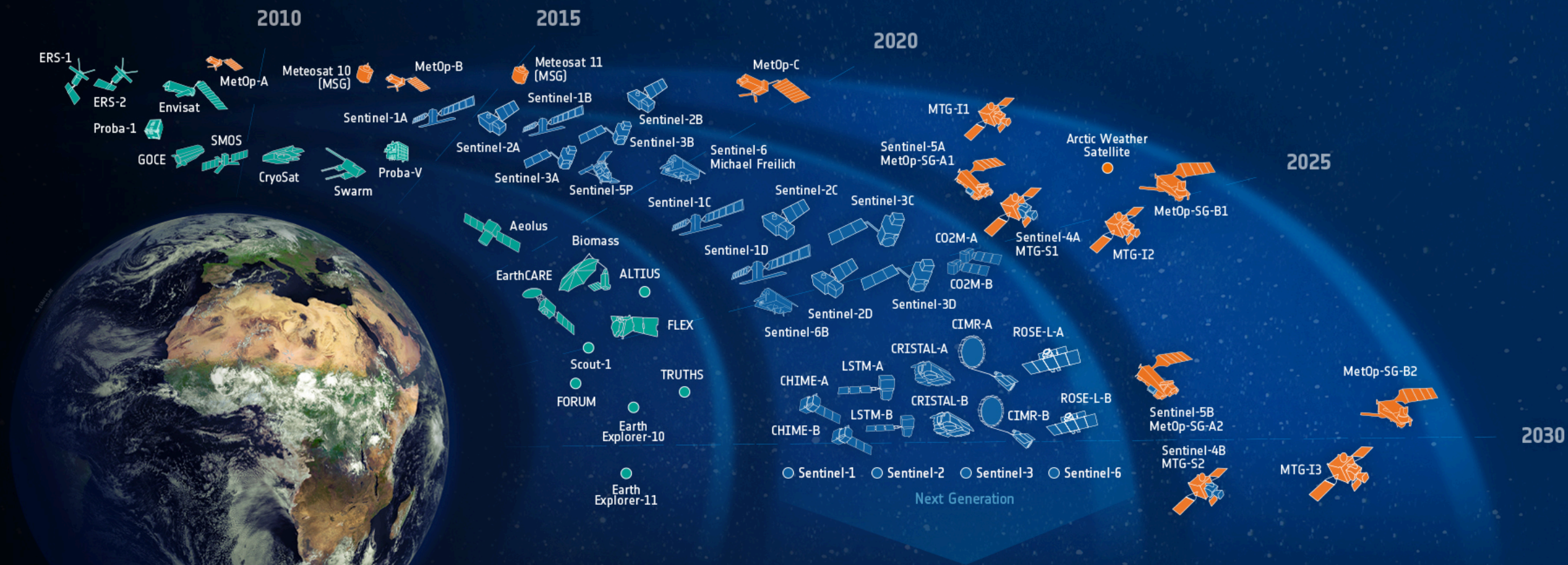


# Some of Today and Tomorrow's Science Missions (2)





# ESA-DEVELOPED EARTH OBSERVATION MISSIONS



Science



Copernicus



Meteorology



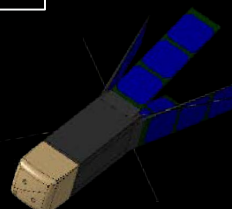


- The ExPeRT programme defines and performs the initial phases of exploration missions to identify critical technologies and contribute to making them reality.
- ExPeRT is committed to establish collaborations with agencies, industries and academia to create exploration opportunities and welcomes the involvement of newcomers and small entities.

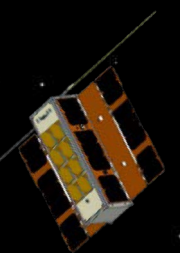




Definition  
Implementation  
Operation



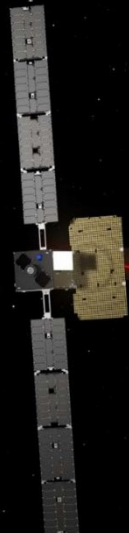
**QARMAN (3U)**  
studying atmosphere re-entry



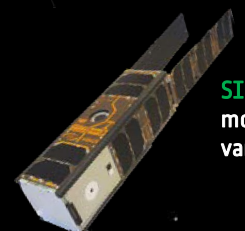
**PRETTY (3U)**  
demonstrating GNSS reflectometry



**GENA-SAT (6U & 12U)**  
demonstrating commercial IOD/IOV services



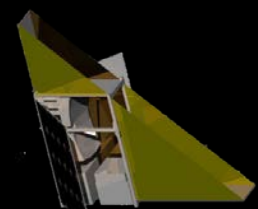
**M-ARGO (12U)**  
demonstrating asteroid rendezvous and identifying in-situ resources



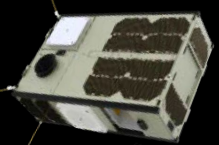
**SIMBA (3U)**  
monitoring climate variables



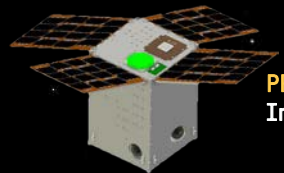
**GOMX-5 (12U)**  
demonstrating next generation constellation technologies



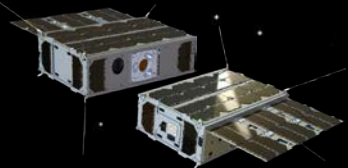
**CubeSpec (6U)**  
stellar spectroscopy from space



**GOMX-4B (6U)**  
demonstrating constellation technologies



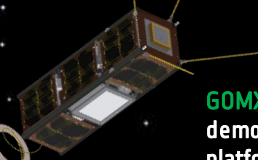
**PROBA-V Companion (12U)**  
Imaging Vegetation



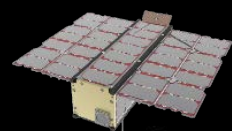
**RACE (2x6U)**  
demonstrating rendezvous and docking



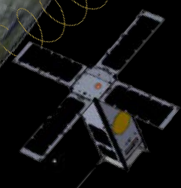
**Juventas & Milani (2x6U)**  
observing asteroid deflection assessment (HERA S2P)



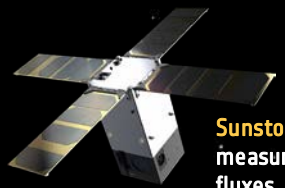
**GOMX-3 (3U)**  
demonstrating new platform technologies



**RadCube (3U)**  
measuring space radiation and magnetic field



**PICASSO (3U)**  
studying the atmosphere



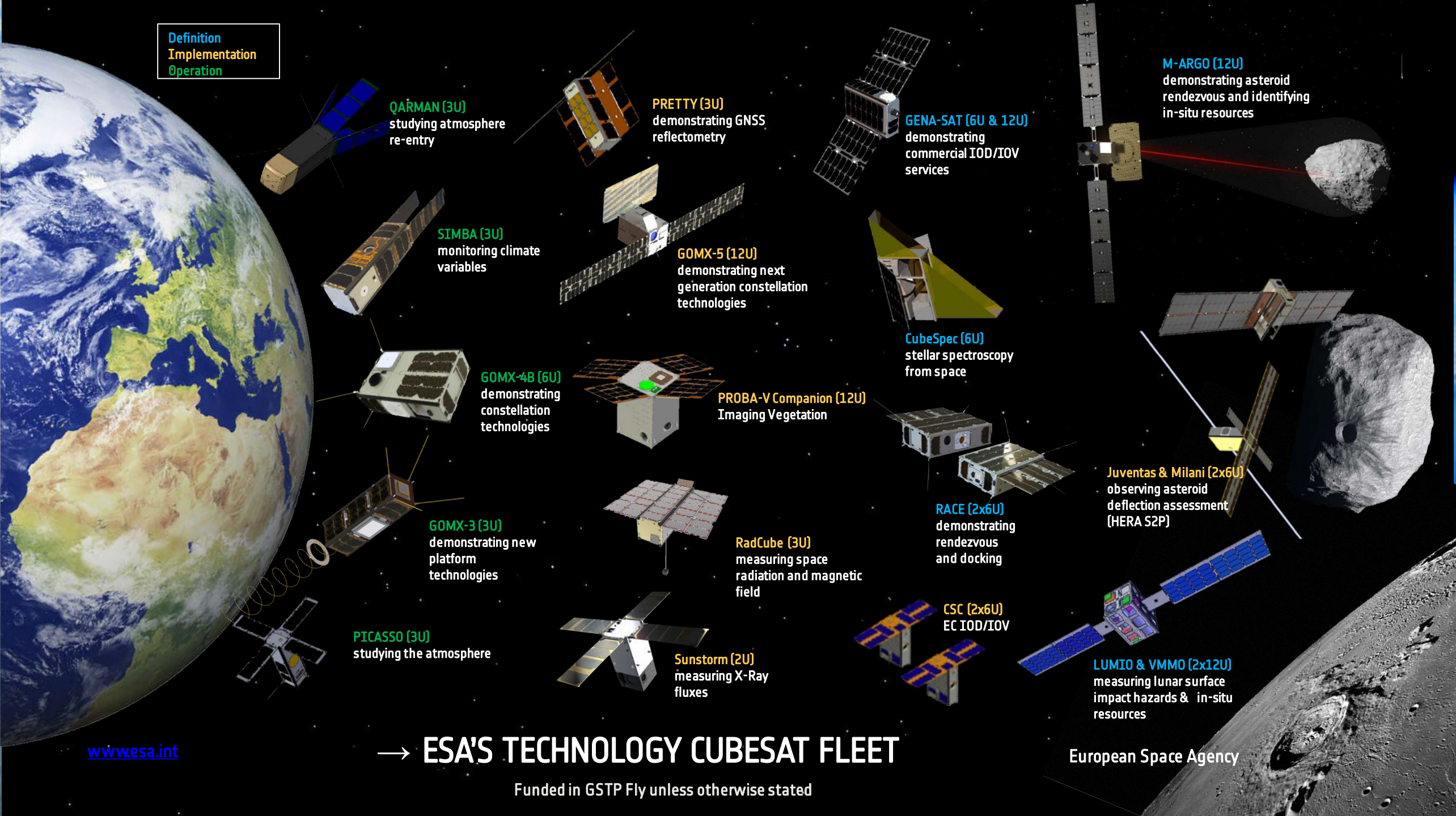
**Sunstorm (2U)**  
measuring X-Ray fluxes



**CSC (2x6U)**  
EC IOD/IOV



**LUMIO & VMMO (2x12U)**  
measuring lunar surface impact hazards & in-situ resources

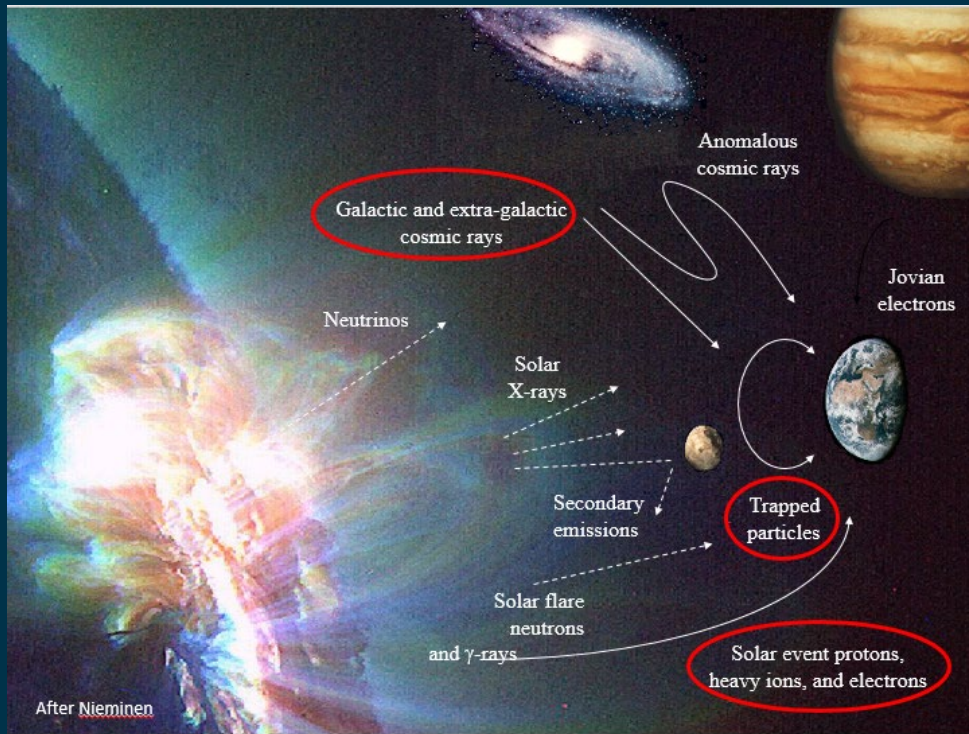


# Space Radiation and Effects on Electronics

Radiation belts trapped by planets' magnetospheres, consisting mostly of protons and electrons

Particles originating from the activity of the Sun, which include also heavy ions

Cosmic rays with very high energy



### Ionising radiation in space

| Particle   | Energy range    |     |         |        |        |     |
|------------|-----------------|-----|---------|--------|--------|-----|
|            | ev              | keV | 10MeV   | 100MeV | 500MeV | GeV |
| Electrons  | ←---TID---→     |     |         |        |        |     |
|            |                 |     | ←-DD-→  |        |        |     |
|            |                 |     | ←-SEE-→ |        |        |     |
| Protons    | ←-----TID-----→ |     |         |        |        |     |
|            |                 |     | ←-DD-→  |        |        |     |
|            |                 |     | ←-SEE-→ |        |        |     |
| Heavy ions | ←-----TID-----→ |     |         |        |        |     |
|            |                 |     | ←-DD-→  |        |        |     |
|            |                 |     | ←-SEE-→ |        |        |     |

### Effect on the component

#### Total Ionising Dose

Electron-hole pairs generation in semiconductor oxides

#### Displacement Damage

Lattice Displacement Damage caused by energetic particles

#### Single event effects

Ion deposits significant charge within device that directly affects its operation



# Mission SEE RHA Process (ref ECSS-Q-ST-60-15C)

Mission SEE Radiation environment

- GCR, Solar particle event, Trapped and solar protons fluxes versus LET spectrum

Table 5-5: Environment to be assessed based on LETth

| Device LETth (MeVcm <sup>2</sup> /mg) | Environment to be assessed   |
|---------------------------------------|--|
| LETth < 15                            | Heavy ions (GCR, solar event ions)<br>Protons (trapped, solar event protons) |
| LETth = 15-60                         | Heavy ions (GCR, solar event ions)   |
| LETth > 60                            | No analysis required   |

No SEE shall cause damage to a system or a subsystem or induce performance anomalies or outages not compliant with mission specifications

Each EEE parts shall be assessed for sensitivity to SEE

- IC, MMIC, MOSFETs N/P, CCD, Opto

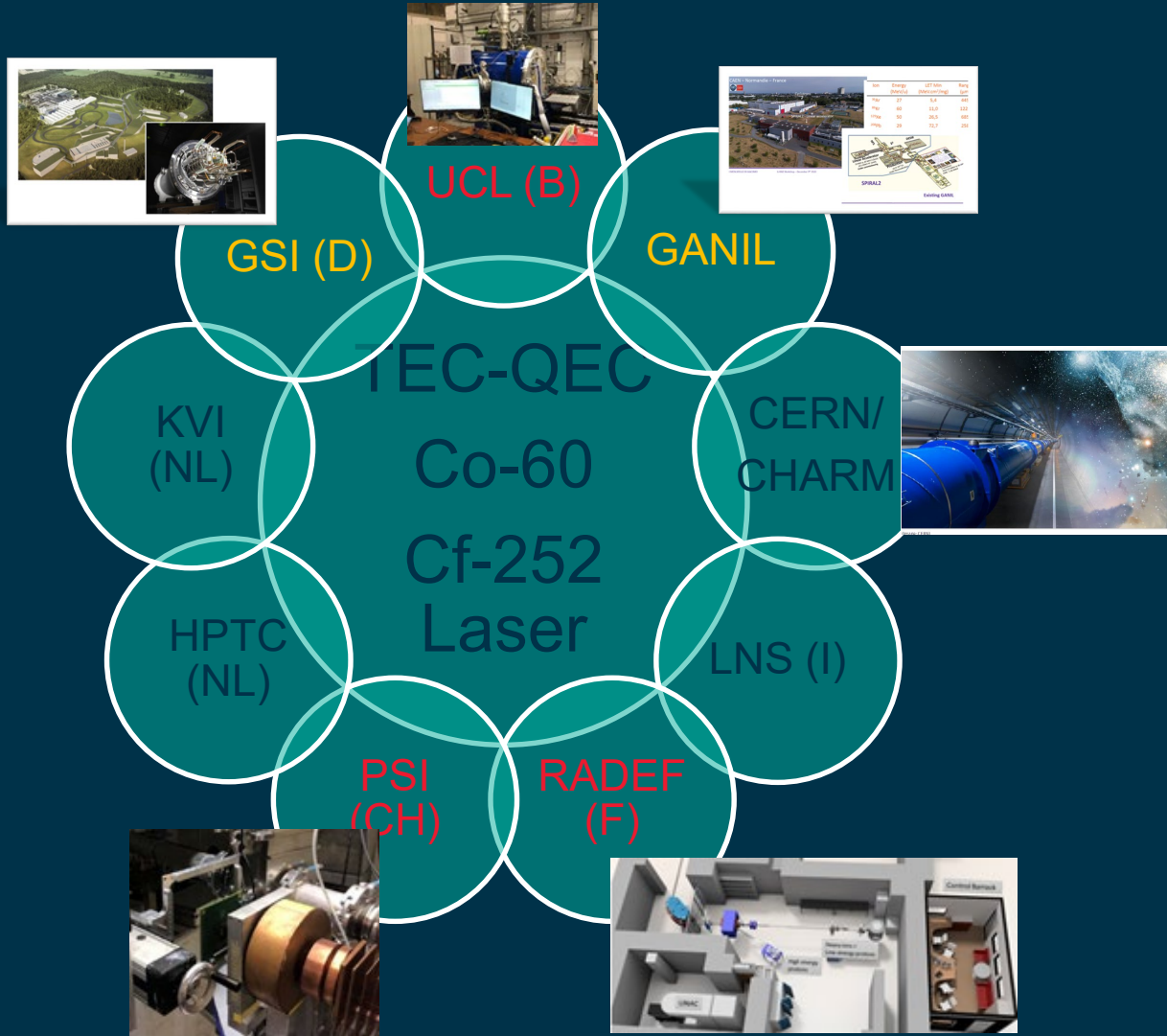
Alternative Sources: Cf-252, Focused Pulsed Laser, Neutron, Alpha sources

SEE Tests Sources HI, Proton

- MIL-STD-750 TM1080, ESCC25100, EIA/JESD 57

Alternative sources shall not be used for SEE qualification. They can be used to check the test H/W and S/W and to investigate the device relative hardness or specific failure modes as a function of device operations

# European Irradiation Facilities for SEE Test



<https://irradiation-facilities.web.cern.ch/>



# European Irradiation Facilities for SEE Test

## Beam Energies

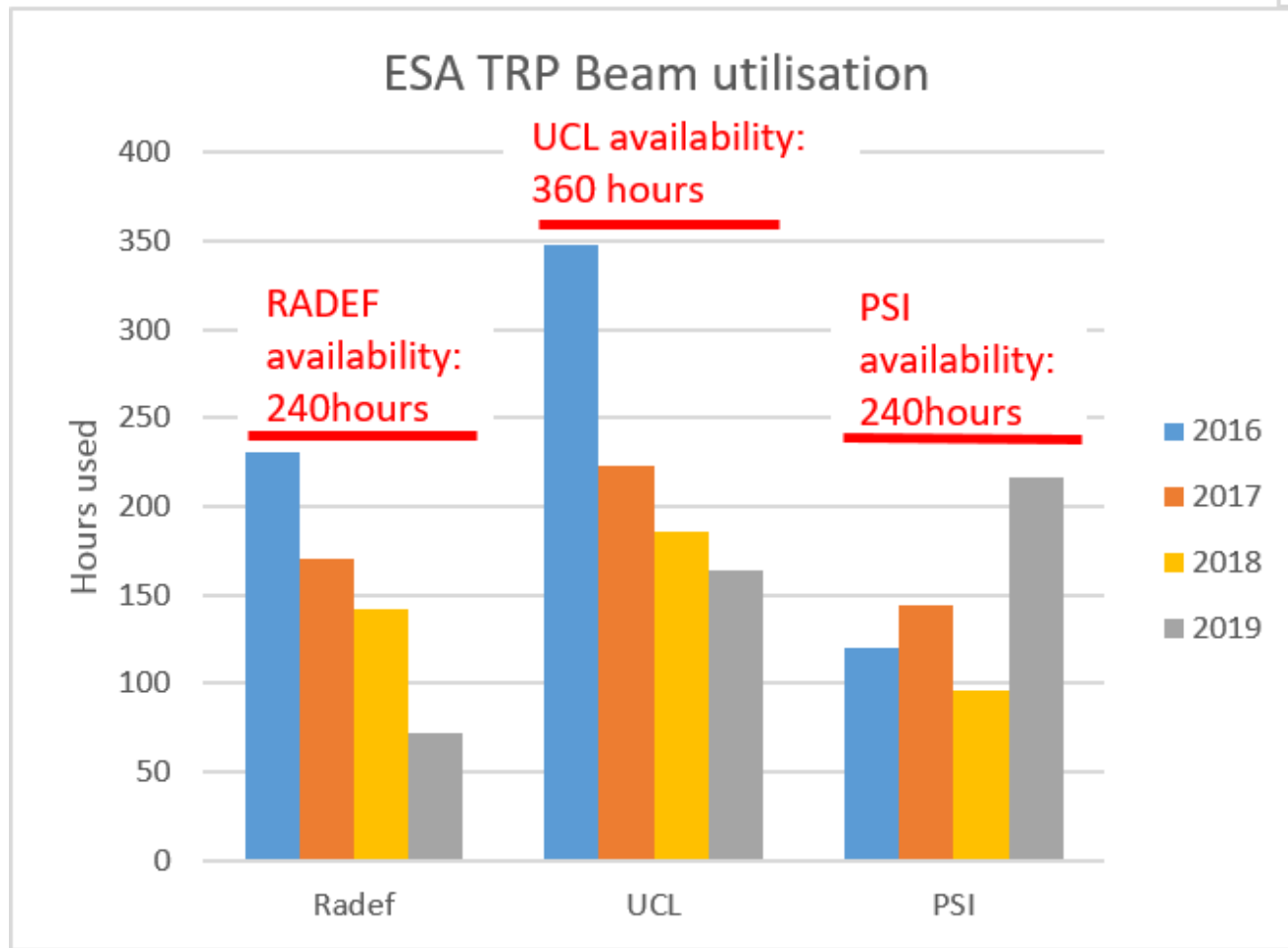
## Availability

|                   |                     |
|-------------------|---------------------|
| Standard Energy   | <10 MeV/n           |
| High Energy       | 10 - 100 MeV/n      |
| Very High Energy  | 100 MeV/n – 5 GeV/n |
| Ultra High Energy | 5-150 GeV/n         |

| Facilities  | Energy (MeV/nucleon)                             | Available cocktail  | Availability per year                           |
|---|--|---|---|
| <b>UCL HIF (Louvain-la- Neuve, Belgium)</b>           | 8-10 MeV/n                                       | 9 species from C to Xe  | About 16 weeks                                  |
| <b>RADEF (Jyväskylä, Finland)</b>                     | 22 MeV/n ,<br>16.3 MeV/n,<br>9.3 MeV/n<br>before | O, Fe, Kr<br>6 ion species, from O to Xe<br>(7 ion species, from N to Xe) | About 12 weeks                                  |
| <b>KVI CART (Groningen, Netherlands)</b>              | 30 MeV/n   | 4 species, from Ne to Xe  | 1-2 weeks                                       |
| <b>GANIL G4 (Caen, France)</b>                        | 27 to 60MeV/n                                    | One species per experiment, Ar, Kr, Xe or Pb                              | 1-2 weeks                                       |
| <b>GSI SIS18 (Darmstadt, Germany)</b>                 | 50 MeV/n to 1-1.5 GeV/n                          | One species per experiment, can be from proton to U                       | Less than 1 week<br>Only scientific experiments |
| <b>CERN CHARM or North Area (Geneva, Switzerland)</b> | 6-160 GeV/nucleon                                | One species per experiment  | Less than 1 week                                |

[Ref: The challenges of Testing at European Irradiation Facilities  
A. Pesce, A. Costantino  
ESCCON2021]

# ESA beam time used at ESA supported facilities



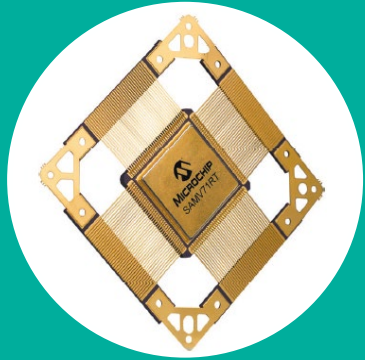
Aim at support facilities developments on **beam quality, dosimetry** and includes an annual fixed amount of hours for irradiations tests for **ESA R&D developments**

2021\_02\_24 CMOS image sensor development  
 2021\_02\_23 SDRAM memories  
 2021\_02\_23 SiC qualification and other mosfet screening  
 2021\_02\_18 TIR(detector)  
 2021\_01\_21 HERA  
 2020\_10\_07 ASIC  
 2021\_01\_18 GaN MIM Capacitors  
 2020\_12\_11 Small study - intradie SRAM testing  
 2021\_11\_24 HERA - cubesat payload only  
 2020\_11\_23 SEE laser COTS screening  
 2020\_11\_22 FYS  
 2020\_11\_02 MEMS pressure modues  
 2020\_10\_16 Latchup testing of digital isolator  
 2020\_10\_09 GPU

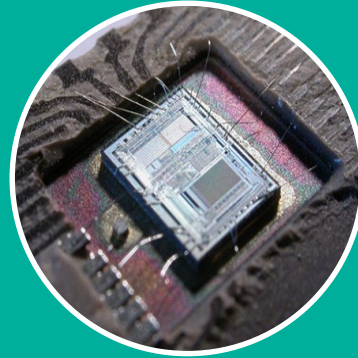
2020\_09\_28 Phototransistor  
 2020\_09\_08 RACOCO  
 2020\_09\_07 MPCG  
 2020\_09\_06 GPU processors  
 2020\_09\_04 RADEM  
 2020\_09\_03 3Dnand  
 2020\_09\_01 GaN Devices  
 2020\_09\_02 SET  
 2020\_09\_01 Stuck bits on SDRAM  
 2020\_08\_31 Optical Fibers  
 2020\_08\_30 Stuck bits on SDRAM  
 2020\_08\_10 Proba 3  
 2020\_08\_09 NG-LARGE  
 2020\_08\_08 NG-ULTRA



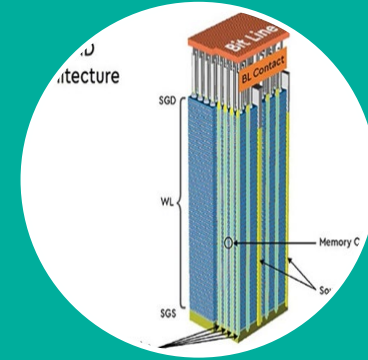




RAD-HARD parts  
Developed and  
Qualified for  
Space



Rad tolerant  
Devices

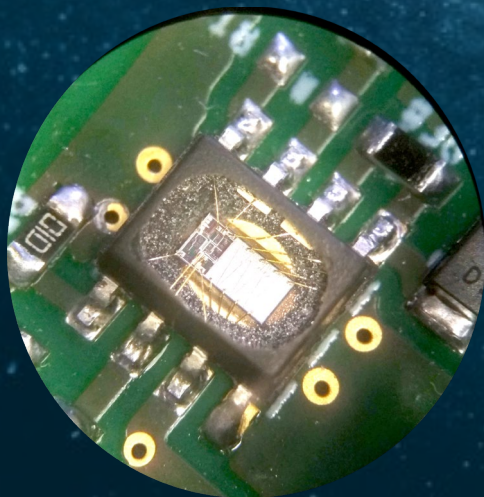


COTS



# Challenges: Limited range of heavy ions at Low Energy

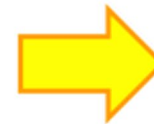
Standard energy ions require sample preparation, delidding/decapping or Die thinning for flip chip to reach the active area with sufficient LET for testing and it may be not technically possible for certain technologies



One common particularity of EEE COTS components is the dense packaging

Examples:

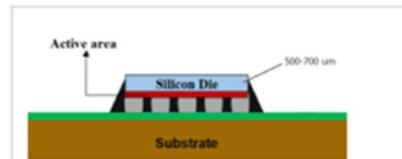
- Multi chip modules
- Flip chip construction
- Hybrids
- Plastic package with Cu bondwires



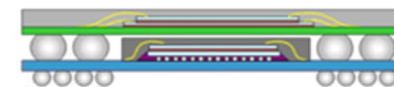
The exposure of either the dies of such packages is either **impossible** or **difficult**, And there is the risk to modify the device response.



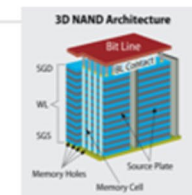
need of more energetic particles to have more range (despite lower LET)



~700um  
**Flip chip:**  
Active area facing package  
Backside irradiation ->  
die thinning



~2mm  
**System in package:**  
Test separately



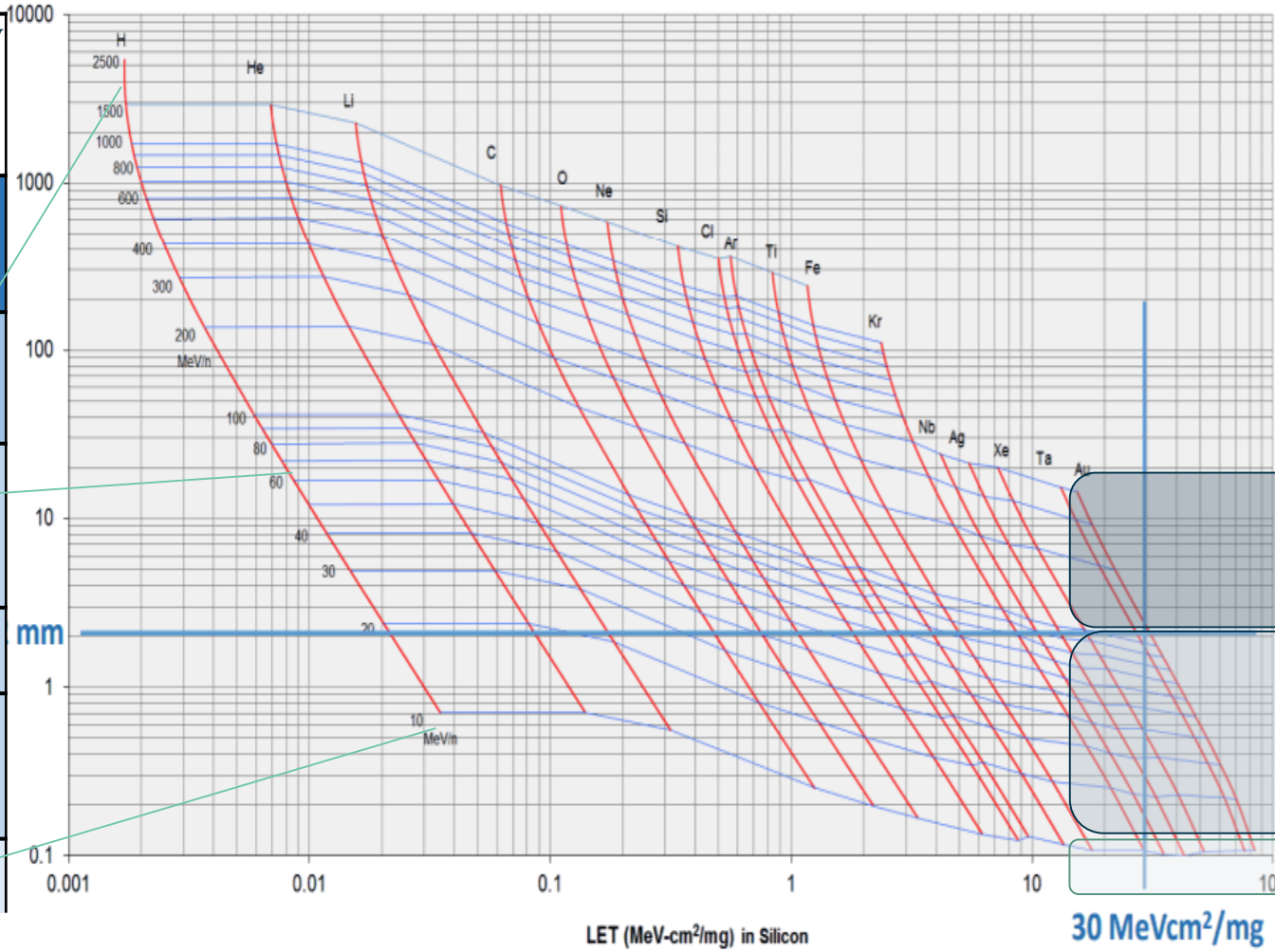
~500um  
**Dense structure:**  
Higher beam penetration range



# Linear energy transfer and range

Range vs. LET

| Facilities        | Energy (MeV/nucleon)            | Range of heavy species (Xe) in silicon                     |
|-------------------|---------------------------------|--|
| <b>CERN CHARM</b> | 6-160 GeV/nucleon               | meters   |
| <b>GSI SIS18</b>  | 50 MeV/n to 1-1.5 GeV/n         | 2.4 mm to 7.8 cm   |
| <b>GANIL G4</b>   | 27 to 60 MeV/n                  | 50 $\mu\text{m}$ to 685 $\mu\text{m}$                      |
| <b>KVI CART</b>   | 30 MeV/n                        | 333 $\mu\text{m}$  |
| <b>RADEF</b>      | 22 MeV/n, 16.3 MeV/n, 9.3 MeV/n | 255 $\mu\text{m}$<br>155 $\mu\text{m}$<br>92 $\mu\text{m}$ |
| <b>UCL HIF</b>    | 8-10 MeV/n                      | 73 $\mu\text{m}$   |



Very High energy

High energy

Standard energy

# HI High Energy facilities- Challenges

## Europe

| Facilities                            | Energy (MeV/nucleon)    | Availability per year                                   |
|---------------------------------------|-------------------------|---|
| <b>GANIL G4 (Caen, France)</b>        | 27 to 60 MeV/n          | <b>1-2 weeks</b>  |
| <b>GSI SIS18 (Darmstadt, Germany)</b> | 50 MeV/n to 1-1.5 GeV/n | <b>Less than 1 week<br/>Only scientific experiments</b> |

## USA

| Facilities                             | Energy (MeV/nucleon)                 | Availability per year                            |
|--|--------------------------------------|--|
| <b>TAMU (College Station, TX, USA)</b> | 15 MeV/n<br>25 MeV/n<br>40 MeV/n     | About 20-25 weeks                                |
| <b>NSRL (Brookhaven, USA)</b>          | 1500-217 MeV/n (light to heavy ions) | ~20 weeks<br>NASA funded or scientific proposals |

**Lack of radiation testing opportunities of High Energy Ion beams**  
**Currently only facilities in USA offer extensive High Energy Ion beams**

GANIL - Grand Accélérateur National d'Ions Lourds  
 CAEN - Normandie - France

| Ion               | Energy (MeV/u) | LET Min (MeV.cm <sup>2</sup> /mg) | Rang (μm) |
|-------------------|----------------|-----------------------------------|-----------|
| <sup>36</sup> Ar  | 27             | 5,4                               | 445       |
| <sup>86</sup> Kr  | 60             | 11,0                              | 1223      |
| <sup>129</sup> Xe | 50             | 26,5                              | 685       |
| <sup>208</sup> Pb | 29             | 72,7                              | 258       |

Labels in image: Cyclotrons, SPIRAL2 - Linear accelerator, DESIR, Linear Accelerator, Production, Existing GANIL

**GANIL**

After:  
**GRAND ACCELERATEUR NATIONAL D'IONS LOURDS**  
 Marie-Hélène MOSCATELLO DI GIACOMO for the, G-RAD Workshop 2020

**GSI**



# Requirements of beam quality for testing 1/3



Ref ESCC25100 SINGLE EVENT EFFECTS TEST METHOD AND GUIDELINES

<https://escies.org/specfamily/view>

| Requirement | ESCC25100   | => Facility implementation   |
|-------------|---|--|
| LET         | <p>the device is commonly considered immune to SEE if tested in normal incidence at a minimum LET of 60MeV.cm2/mg</p> <p>There is an increasing need to perform SEE test at lower and lower LET thresholds. LET disposeure between 0.2 MeV/mg/cm<sup>2</sup> and 1.5 MeV/mg/cm<sup>2</sup>. If possible implement a disposeure of 4 LETs within this range</p> <p>Combination of ions, light to heavy species, covering LET at least equal to 38 MeVcm2/mg (Si) up to 60 MeVcm2/mg (Si) at the device sensitive volume, and with range at least of 1 mm (Si).</p> | <p><b>LET up to 60MeV.cm2/mg</b><br/>to consider a device immune to SEE (ECSS-Q-ST-60-15)</p> <p><b>LET up to 75MeV.cm2/mg</b><br/>to consider a device immune to SEE ref NASA/TM-20210018053</p> <p><b>LET 10-60MeV.cm2/mg</b><br/>necessary to estimate cross section</p> <p><b>LET &lt; 2 MeV.cm2/mg</b><br/>Advances technology nodes show an increase in SEE sensitivity at very low LETs</p> |
| Range       | <p>a minimum range of 40µm in the target material is recommended. In linear devices and all devices with a relatively thick sensitive volume (&gt;10µm like in bipolar, JFET, etc.), a minimum range of 60µm is recommended. If technology analysis is available the beam energy and range should be such that the Bragg peak is placed beyond the sensitive volume.</p>  | <p>Range &gt;60um up to few mm</p>   |
| Temperature | <p>The <b>temperature</b> of the device under test shall be monitored and recorded unless otherwise agreed with the Customer.</p>   | <p>Monitored as minimum,<br/>control of temperature (eg for SEL )</p>  |



# Requirements of beam quality for testing 2/3



Ref ESCC25100 SINGLE EVENT EFFECTS TEST METHOD AND GUIDELINES

<https://escies.org/specfamily/view>

| Requirement                          | ESCC25100  | => Facility implementation   |
|--------------------------------------|--|--|
| Tilting to explore other LETs values | For LETs not directly available, the device may be tilted to give an increased "effective LET"                                   | Frame that can tilted (remotely)                                   |
| Flux and energy uniformity           | The radiation field shall be uniform to $\pm 10\%$ over the area of the device(s) under test in terms of both fluence and energy | $\pm 10\%$ over the area of the device(s) for both energy and flux |
| Flux min-max                         | few 10 ions/cm <sup>2</sup> /s to at least 10E5 ions/cm <sup>2</sup> /s  | Typical fluxes 1E4 – 1E6 ions/cm <sup>2</sup> /s                   |





# Requirements of beam quality for testing 3/3

Ref ESCC25100 SINGLE EVENT EFFECTS TEST METHOD AND GUIDELINES

<https://escies.org/specfamily/view>

| Other general considerations                    |  |
|---|--|
| Positioning DUTs                                | <p>Standard frame with design available to customer for preparation (eg see UCL frame on ESCIES.org radiation page)<br/>SEE Standard board SEE ref ESCC25100</p> <p>Remote accurate control of the frame : multiple DUTs mounted on frame to be moved in the beam and testing without accessing/breaking vacuum</p> <p>Laser pointer for accurate positioning<br/>Visual feedback (camera) for correct positioning</p> <p>Vacuum Chamber Requirements (ref MIL-STD-750 TM1080)</p> |
| Timing  | <p>Timing<br/>1-2 hours for calibrations to set the cyclotron<br/>15 min to change ions<br/>15 min to access DUTs (vacuum )</p>  |
| Cabling   | <p>Feedthroughs flanges and cable distances to be considered.<br/>Possibility to have test and monitoring equipment installed close to the beam line and accessible</p>  |
| Space in control room/preparation of experiment | <p>Additional area to prepare the SEE test set up and perform dry run</p>  |

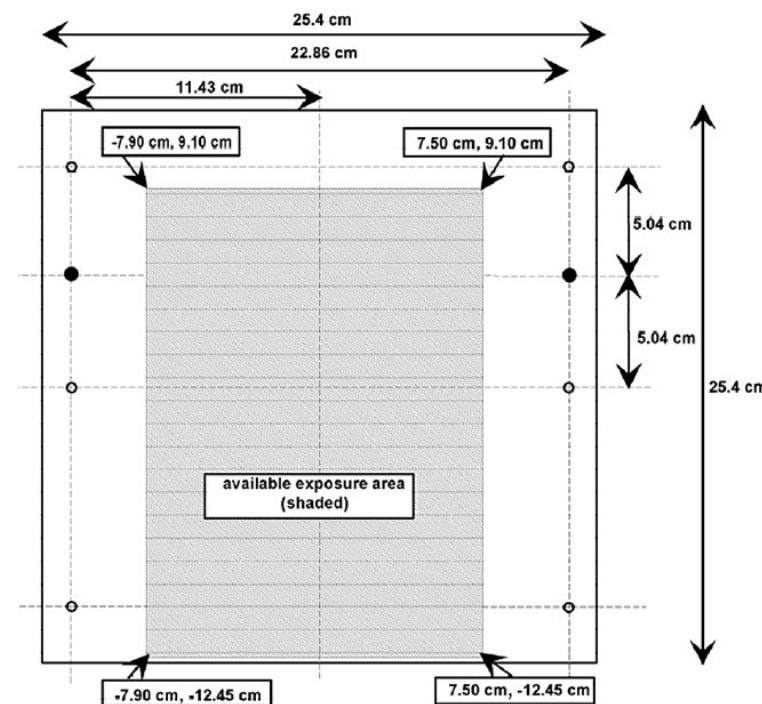


ESCC Basic Specification No. 25100

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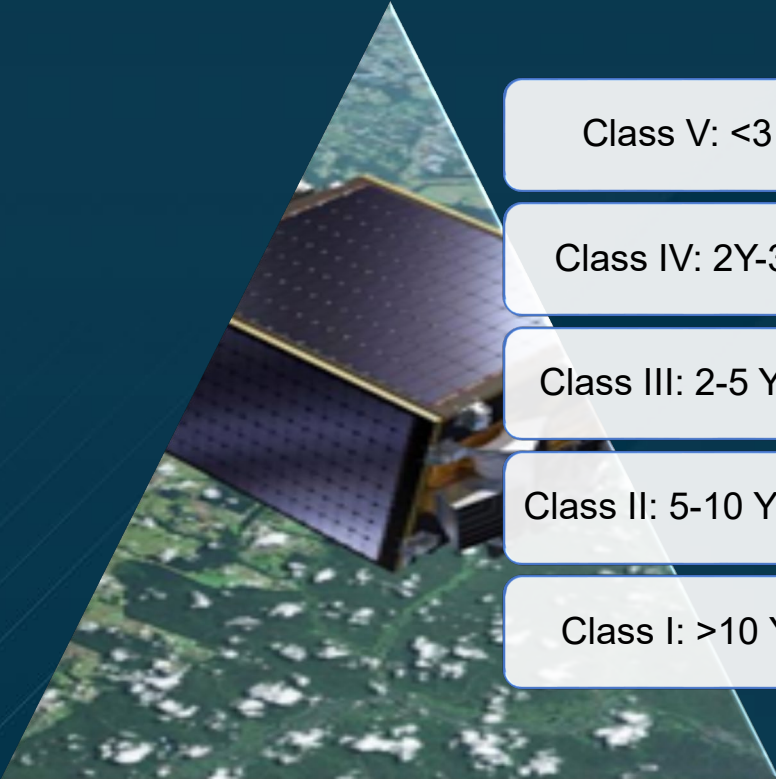
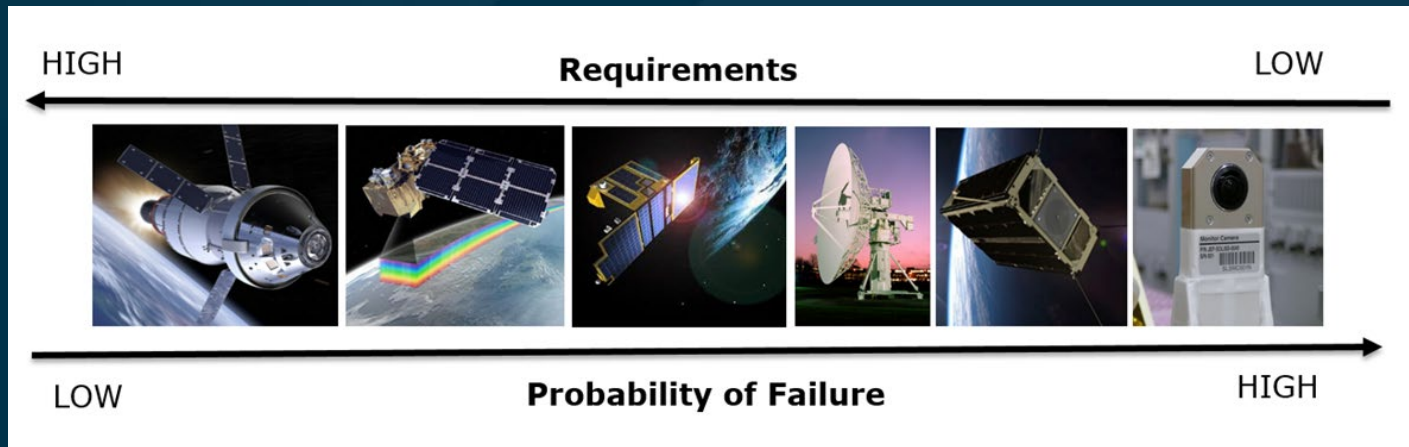
ISSUE 2

FIGURE 1 – EXAMPLE OF AN SEE TEST BOARD



# Evolution of the ESA Mission Requirements

New approach for optimising resources in accordance with mission profiles and objectives  
New working methods aiming at reducing development time and cost while balancing risk



- Class V: <3 M, <1ME
- Class IV: 2Y-3M 50-1ME
- Class III: 2-5 Y/50-200 ME
- Class II: 5-10 Y/200-700 ME
- Class I: >10 Y/>700 ME



# Evolution of the RHA Strategy

- **5 Classes, 4 different sets of requirements tailored from ECSS-Q-ST-60-15**
- Class V: Suggested to have a separate standard- Perhaps only PARD



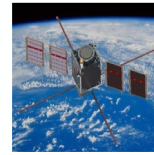
## Class V

- < 3 M
- No TID test
- **NO SEE test** except for MOSFET VDS > 200V
- Proton Test recommended (component or board level)
- No heavy ion test data are required except for MOSFET > 200V
- Proton Test is recommended (component or board level)



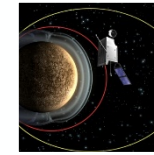
## Class IV

- 3M-2y
- No TID test if TIDL<5Krad
- **SEE** HI test **recommended**
- **Proton test required**
- 15 MeVcm<sup>2</sup>/mg < LET<sub>th</sub> < 38 MeVcm<sup>2</sup>/mg Heavy ion SEE analysis required
- LET < 15 MeVcm<sup>2</sup>/mg Heavy ion and proton SEE analysis required



## Class III

- 2y -5 y
- No TID if TIDL<5Krad
- HI at part and board level
- Proton at part and board level



## Class I & II

- > 5 y
- ECSS-Q-ST-60-15 + ESSB-Q-008
- TID
- SEE

# ESA Website for Radiation Test data- **NEW**

## <https://esarad.esa.int/>



ESA Radiation Test Database

This database contains radiation test reports of radiation tests (SEE TID DD) on EEE components performed by ESA or by European partners under ESA contracts.

For any further info or enquire please contact: [esarad@esa.int](mailto:esarad@esa.int)

Show 20 entries

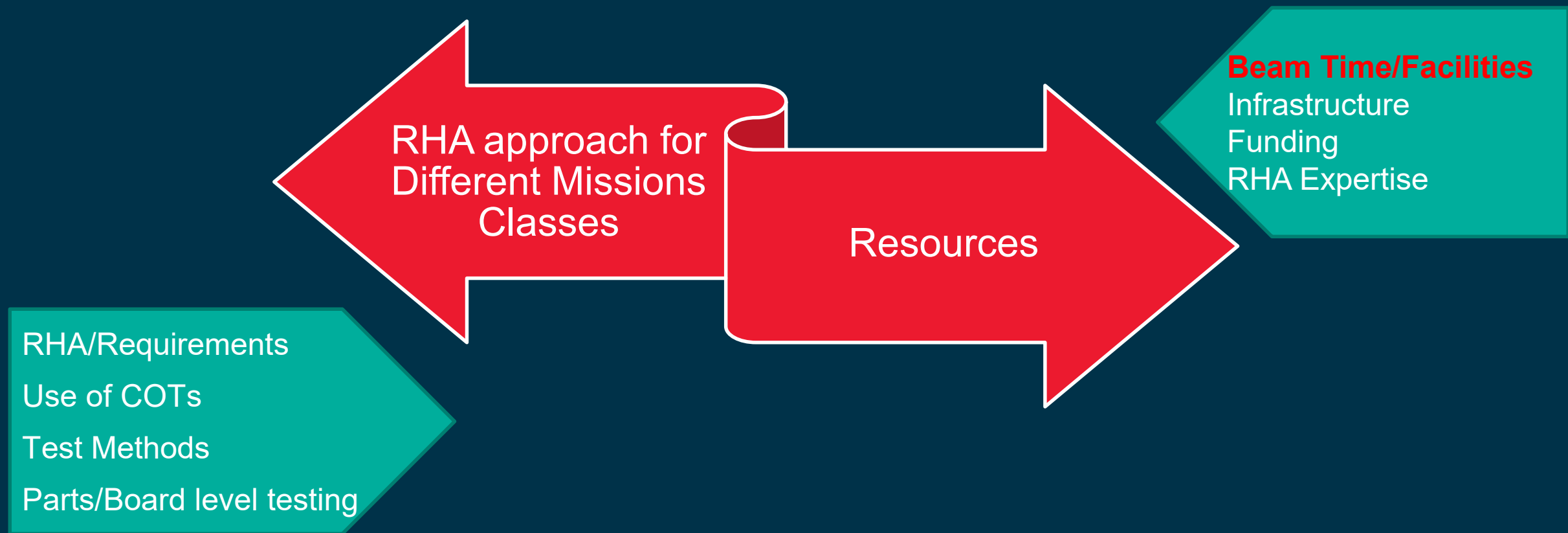
| DUT part type        | DUT Manufacturer                             | Report File              | Radiation Test Type                                      | Radiation Test Method    | EPFL Family         | EPFL Group                              | Function   | Technology | Report Source        | Report Date |
|----------------------|--|--------------------------|--|--------------------------|---------------------|---|--|------------|----------------------|-------------|
| MT39F1208CBACA       | MICRON                                       | <a href="#">Download</a> | SEE (Single Events Effects)<br>TID (Total Ionising Dose) | ESCC 22900<br>ESCC 25100 | 8 MICROCIRCUITS     | 29 MEMORY OTHERS                        | Multi-Level-Cell NAND Flash Memory                                 |            | University of Padova | 01/03/2013  |
| UC2843 and UC2845    | STMicroelectronics                           | <a href="#">Download</a> | SEE (Single Events Effects)                              |                          | 8 MICROCIRCUITS     | 90 OTHER FUNCTIONS                      | Pulse Width Modulator  |            | Hires                | 21/06/2010  |
| ST9H40910S13         | STMicroelectronics                           | <a href="#">Download</a> | TID (Total Ionising Dose)                                |                          | 12 TRANSISTORS      | 6 FET P-CHANNEL                         | Power MOSFET   |            | ESA                  | 02/10/2009  |
| ZN1387               | Microsemi                                    | <a href="#">Download</a> | DD (Displacement Damage)                                 |                          | 12 TRANSISTORS      | 1 LOW POWER, NPN (< 2WATTS)             |  |            | Hires                | 03/06/2011  |
| ZN1514               | Microsemi                                    | <a href="#">Download</a> | DD (Displacement Damage)                                 |                          | 12 TRANSISTORS      | 2 LOW POWER, PNP (< 2WATTS)             |  |            | Hires                | 24/01/2012  |
| GR740 System on chip | Cobham Gasler                                | <a href="#">Download</a> | SEE (Single Events Effects)                              |                          | 8 MICROCIRCUITS     | 10 MICROPROCESS/ MICROCONTROL, PERIPHER | System on chip   |            | Cobham Gasler AB     | 28/09/2020  |
| OA-470A              | Advanced Analog                              | <a href="#">Download</a> | TID (Total Ionising Dose)                                | ESCC 22900               | 8 MICROCIRCUITS     | 50 LINEAR OPERATIONAL AMPLIFIER         | Linear, Radiation Hardened, Low Noise, Quad Operational Amplifiers |            | Altair               | 12/11/2012  |
| UC1846J-SP           | Texas Instrument                             | <a href="#">Download</a> | TID (Total Ionising Dose)                                | ESCC 22900               | 8 MICROCIRCUITS     | 69 LINEAR OTHER FUNCTIONS               | High Speed Pulse Width Modulator Controller                        |            | Altair               | 12/11/2012  |
| PM139M2MLR           | Analog Devices                               | <a href="#">Download</a> | TID (Total Ionising Dose)                                | ESCC 22900               | 8 MICROCIRCUITS     | 53 LINEAR VOLTAGE COMPARATOR            | Quad voltage comparator  |            | Altair               | 12/11/2012  |
| OU1248-86099-4N49    | 4N4811optink, OU124811optink, 86099/Micropec | <a href="#">Download</a> | TID (Total Ionising Dose)                                | ESCC 22900               | 18 OPTO ELECTRONICS | 1 OPTOCOUPLER                           | Photo-Transistor Optocoupler                                       |            | EADS Astrium         | 25/11/2009  |
| UC1843               | Texas Instrument                             | <a href="#">Download</a> | TID (Total Ionising Dose)                                | ESCC 22900               | 8 MICROCIRCUITS     | 69 LINEAR OTHER FUNCTIONS               | Current Mode Pulse Width Modulator                                 |            | Altair               | 11/12/2012  |
| BUL54A               | Semiteab                                     | <a href="#">Download</a> | TID (Total Ionising Dose)                                | ESCC 22900               | 12 TRANSISTORS      | 3 HIGH POWER, NPN (> 2WATTS)            | NPN Power Silicon Transistor                                       |            | Fraunhofer Institut  | 04/12/2018  |
| K894018V1C-T110      | Samsung                                      | <a href="#">Download</a> | SEE (Single Events Effects)                              | ESCC 25100               | 8 MICROCIRCUITS     | 20 MEMORY SRAM                          | 256K x16 Bit High Speed SRAM                                       |            | ESA                  | 30/05/2016  |
| Z571600              | STMicroelectronics                           | <a href="#">Download</a> | TID (Total Ionising Dose)                                | ESCC 22900               | 12 TRANSISTORS      | 4 HIGH POWER, PNP (> 2WATTS)            | PNP High Voltage Transistor  |            | Fraunhofer Institut  | 27/09/2018  |
| 80516                | Semiteab                                     | <a href="#">Download</a> | TID (Total Ionising Dose)                                | ESCC 22900               | 12 TRANSISTORS      | 3 HIGH POWER, NPN (> 2WATTS)            | NPN Power Silicon Transistor                                       |            | Fraunhofer Institut  | 04/12/2018  |
| HCPL3701             | Avago  | <a href="#">Download</a> | SEE (Single Events Effects)                              | Not specified            | 18 OPTO ELECTRONICS | 1 OPTOCOUPLER                           | Optocoupler  |            | TRAD                 | 16/04/2012  |
| AD5658T              | Analog Devices                               | <a href="#">Download</a> | TID (Total Ionising Dose)                                | ESCC 22900               | 8 MICROCIRCUITS     | 62 LINEAR DIGITAL TO ANALOG CONVERTER   | 12-BIT DAC   |            | Altair               | 12/11/2012  |
| OA274QMLR            | Analog Devices                               | <a href="#">Download</a> | TID (Total Ionising Dose)                                | ESCC 22900               | 8 MICROCIRCUITS     | 50 LINEAR OPERATIONAL AMPLIFIER         | Low Noise, Precision Operational Amplifier                         |            | Altair               | 12/11/2012  |
| ZN17370              | Microsemi                                    | <a href="#">Download</a> | TID (Total Ionising Dose)                                | ESCC 22900               | 12 TRANSISTORS      | 3 HIGH POWER, NPN (> 2WATTS)            | NPN Power Silicon Transistor                                       |            | Fraunhofer Institut  | 16/10/2018  |
| 80516                | Semiteab                                     | <a href="#">Download</a> | TID (Total Ionising Dose)                                | ESCC 22900               | 12 TRANSISTORS      | 3 HIGH POWER, NPN (> 2WATTS)            | NPN Power Silicon Transistor                                       |            | Fraunhofer Institut  | 04/12/2018  |

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# RHA in Space: What's Needed/ What's Next?





# ESA Strategy on Radiation Testing Capabilities



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**Info on external facilities**

<https://escies.org/webdocument/showArticle?id=921&groupid=6>

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**Info on ESTEC Co60, Cf 252, SEE Laser Testing**

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# THANK YOU



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